

Silicon PNP Power Transistors

2N6489 2N6490 2N6491

DESCRIPTION

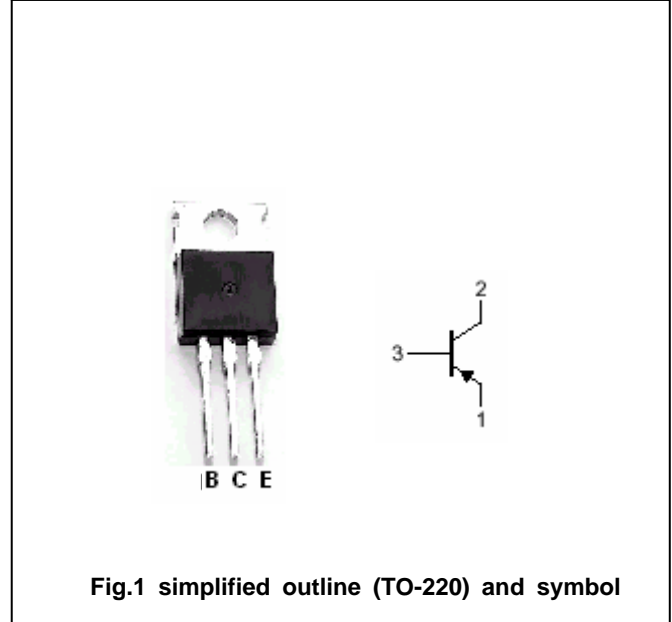
- With TO-220 package
- Excellent safe operating area
- Complement to type 2N6486 2N6487 2N6488 respectively

APPLICATIONS

- Power amplifier and medium speed switching applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

Absolute maximum ratings($T_a=25$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	2N6489	-50	V
		2N6490	-70	
		2N6491	-90	
V_{CEO}	Collector-emitter voltage	2N6489	-40	V
		2N6490	-60	
		2N6491	-80	
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-15	A
I_B	Base current		-5	A
P_T	Total power dissipation	$T_C=25$	75	W
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-65~150	

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal resistance from junction to case	1.67	/W

Silicon PNP Power Transistors

2N6489 2N6490 2N6491

CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CE0(SUS)}	Collector-emitter sustaining voltage	2N6489	I _C =-0.2A ; I _B =0			V
		2N6490				
		2N6491				
V _{CEsat-1}	Collector-emitter saturation voltage	I _C =-5A; I _B =-0.5A			-1.3	V
V _{CEsat-2}	Collector-emitter saturation voltage	I _C =-15A; I _B =-5A			-3.5	V
V _{BE-1}	Base-emitter on voltage	I _C =-5A ; V _{CE} =-4V			-1.3	V
V _{BE-2}	Base-emitter on voltage	I _C =-15A ; V _{CE} =-4V			-3.5	V
I _{CEX}	Collector cut-off current V _{BE} =-1.5V	2N6489				mA
		2N6490				
		2N6491				
I _{CEO}	Collector cut-off current	2N6489				mA
		2N6490				
		2N6491				
I _{EBO}	Emitter cut-off current	V _{EB} =-5V; I _C =0			-1.0	mA
h _{FE-1}	DC current gain	I _C =-5A ; V _{CE} =-4V	20		150	
h _{FE-2}	DC current gain	I _C =-15A ; V _{CE} =-4V	5			

Silicon PNP Power Transistors

2N6489 2N6490 2N6491

PACKAGE OUTLINE



Fig.2 Outline dimensions(unindicated tolerance: ± 0.10 mm)